Abstracts

Modeling the Gate I/V Characteristic of a GaAs MESFET for Volterra-Series Analysis (Short Papers)

S.A. Maas and A. Crosmun. "Modeling the Gate I/V Characteristic of a GaAs MESFET for Volterra-Series Analysis (Short Papers)." 1989 Transactions on Microwave Theory and Techniques 37.7 (Jul. 1989 [T-MTT]): 1134-1136.

This paper shows that the Taylor-series coefficients of a FET's gate/drain I/V characteristic, which is used to model this nonlinearity for Volterra-series analysis, can be derived from low-frequency RF measurements of harmonic output levels. The method circumvents many of the problems of using dc measurements to characterize this nonlinearity.

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